

# A building block for a scalable quantum computing architecture



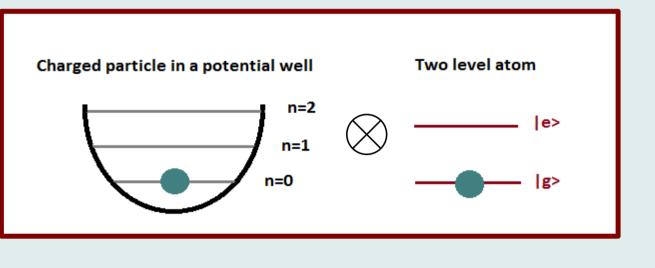
Trapped-Ion Quantum Information Group, ETH Zürich Chiara Decaroli, Maryse Ernzer, Simon Ragg, Jonathan Home

### Towards a scalable quantum computer

#### QCCD architecture: one approach to scalable devices

- Large number of independent trapping units.
- Junctions allow scalability by connecting trap units in two dimensions.
- Quantum information, encoded in the ions, is transferred by physically shuttling the ions to different trap units.
- Integrated optics are necessary for compact and scalable devices.

lon as a qubit: two internal energy levels are identified as the quantum states  $|0\rangle$  and  $|1\rangle$ , two qubits are coupled via their motion.



This work: a double-junction, multi- species

through optical lensed fibres, designed for:

ion trap with integrated laser delivery

-Decoherence Free Subspace (DFS) ion

-manipulation of long chains of ions

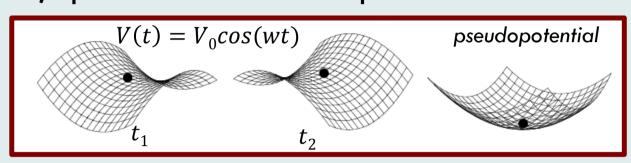
TIQI, ETH, string of ions

transport across the junctions

-parallel operations

Kielpinski et al, 2002

Trapping the ion: RF & DC electric fields confine the ion in all directions, DC fields are used to transport the ions, split and recombine potential wells.



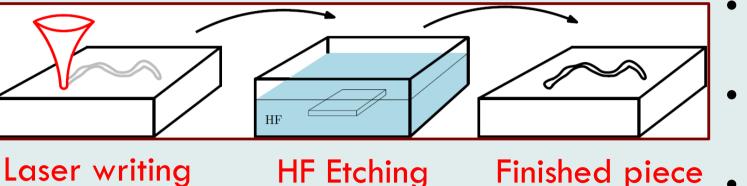
Manipulating the ion: laser light is used to cool the ion, initialize its state and realize a universal set of quantum gates, including two-qubit gates and qubit readout.

THIS WORK: a 3D double junction ion trap with integrated optical delivery for scalable quantum computation

# 1.) Precise wafer alignment

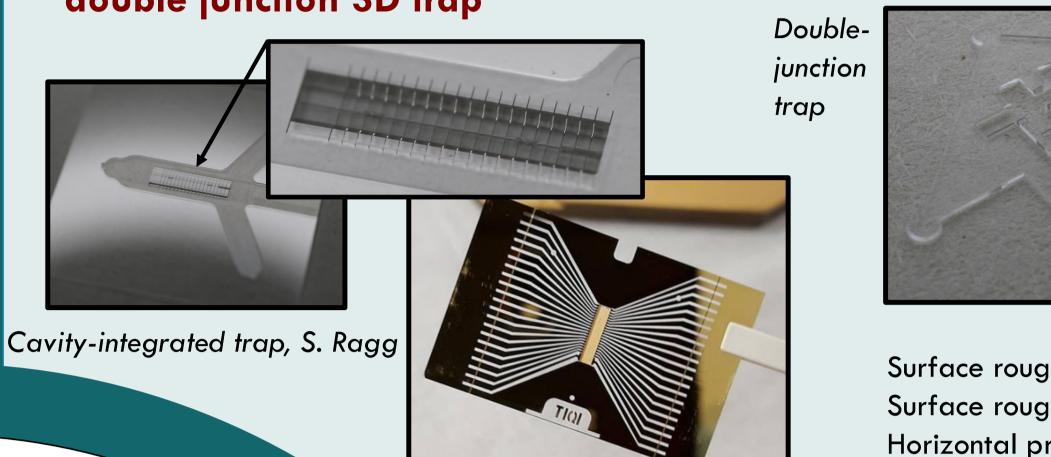
Previous traps alignment: alumina trap wafers manually assembled, leading to misalignment of up to 10  $\mu$ m. Misalignment affects the location of the minimum of the pseudopotential in which the ions are trapped.

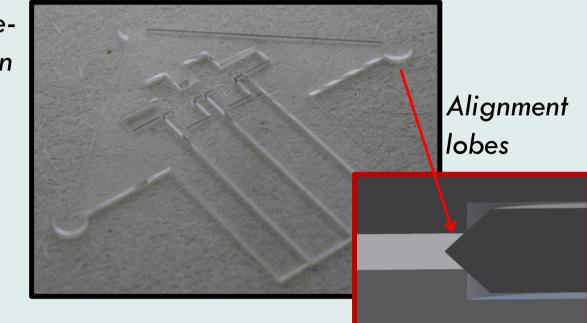
#### New wafer manufacturing technology: subtractive laser writing (FemtoPrint)



- Allows for the creation of small, precise structures on wafers.
- Alignment of wafers by mechanical guides less prone to misalignment errors. Easy, fast and precise assembly.

Our new traps using this technology: a cavity integrated 3D trap and a double junction 3D trap





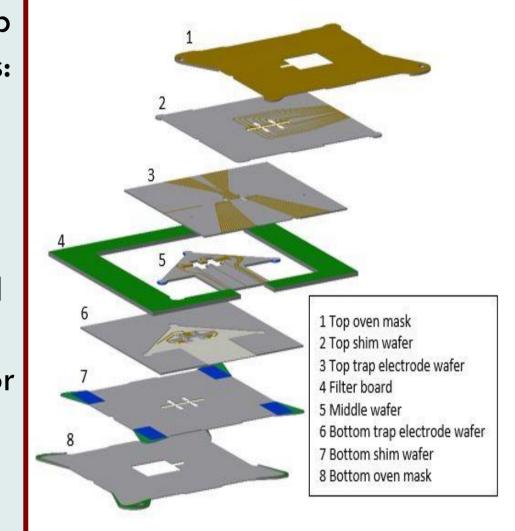
Surface roughness 3D surfaces < 200 nm Surface roughness vertical < 80 nm Horizontal precision  $\approx 1 \, \mu m$ vertical precision  $\approx 5 \ \mu m$ 

Double junction trap consists of 7 wafers:

-two main trapping wafers -middle wafer (spacer and optical integration) -two shim wafers for compensation -two oven masks

Side view: optical access angle

and electrodes distance



Design & trapping zones

-145 total electrodes (ca 100

-two main trapping wafers (total

-electrode-ion distance: 185 μm

-three independent experimental

2. Double junction trap

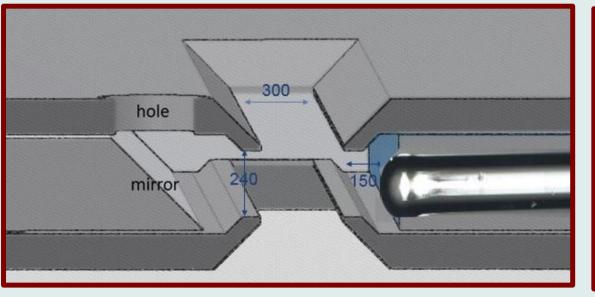
-two X junctions

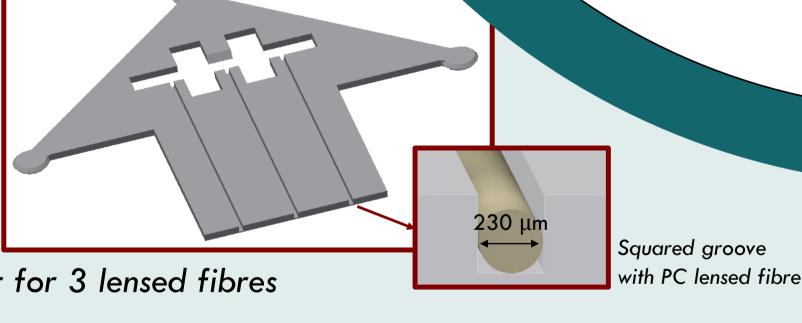
stack of 7).

control electrodes).

## 3. Optical integration: lensed fibres

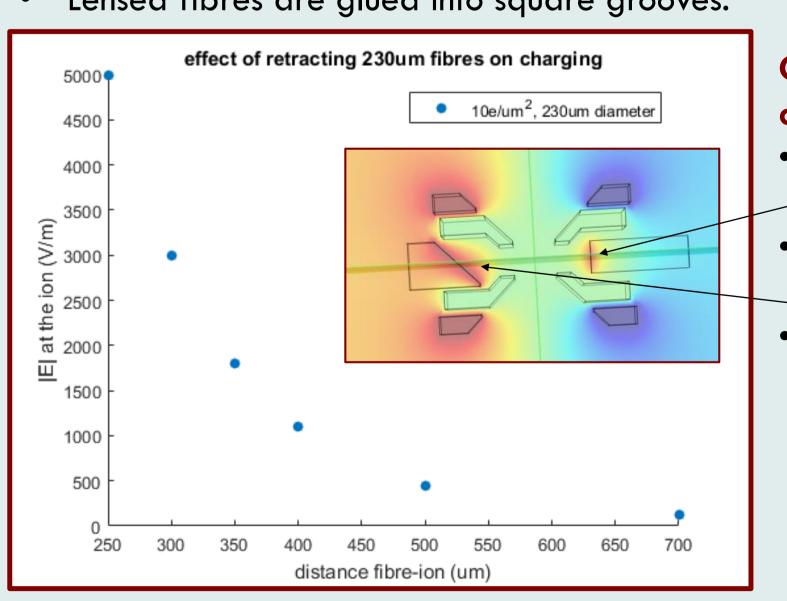
Previous technology: ions are addressed using free space laser beams: requires bulky optics and custom objectives, not easily scalable.

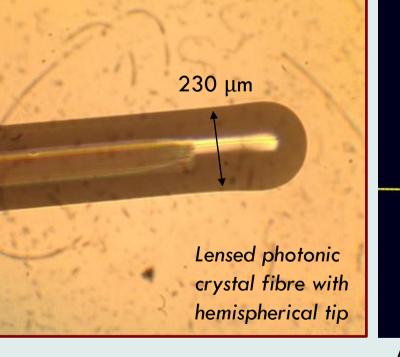


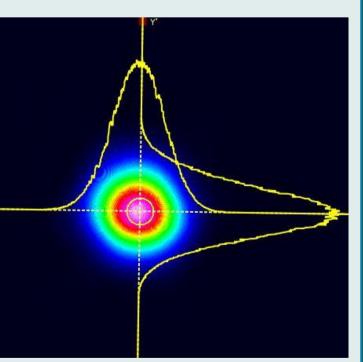


The middle wafer serves as a holder for 3 lensed fibres

- Lensed fibres bring laser light to the ions at the experimental zones.
- Photonic Crystal Fibres (PCFs) have lenses at their tip to focus the light to 20  $\mu$ m (FWHM), up to  $500 \ \mu m$  away.
- Lenses produced via rounds of polishing.
- Hemispherical lens creates a Gaussian beam profile (Fig. on the right).
  - Lensed fibres are glued into square grooves.





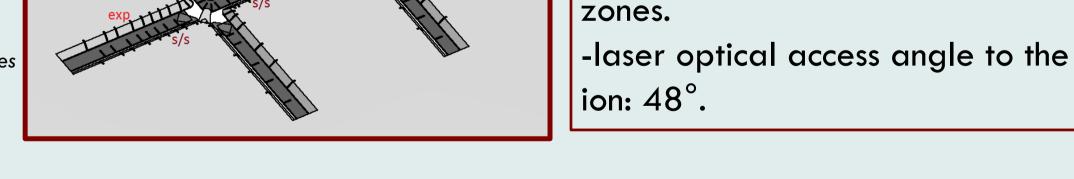


Measured beam profile after lens

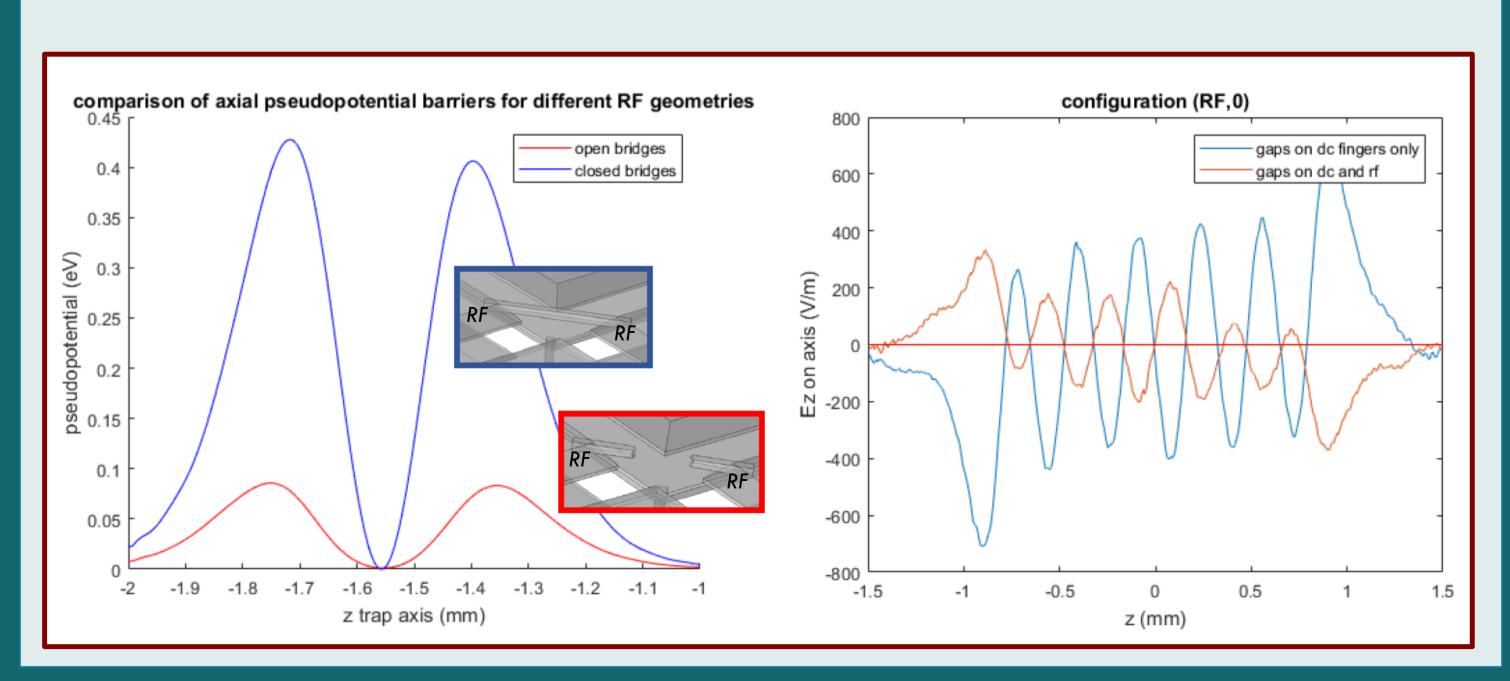
#### Challenges and solutions of integrating optics

- Glass fibres tip accumulates charges, producing stray electric fields.
- Solution: bias electrodes serving also as mirrors for extracting light from setup.
- Alternative: coat fibres with Indium Tin Oxide (ITO), to make them electrically shielding, yet transparent at IR wavelengths (700-800 nm). Expected transparency 70-

### Top view: double junction with segmented electrodes



- Symmetry of the electric fields needs to be broken to confine at the centre of the junction.
- Bridges connecting the RF electrodes break the symmetry but introduce axial pseudopotential barriers (Fig. below: FEM simulation of pseudopotential on axis).
- Shaping RF bridges allows for pseudopotential barrier's height minimization.
- Open bridges create lower pseudopotential barriers (0.1-0.2 eV) than full bridges.
- Segmenting the RF electrodes like the DC electrodes reduces micromotion.



### Outlook

-Fabrication of the trap carried out in the ETH cleanroom using electron beam evaporation of gold.

85 %.

-Experiments with the double junction trap: DFS ion transport across junctions, parallel control of ions, manipulation of long chains of ions towards the understanding of condensed matter problems.